

**In the Claims:**

Please cancel claims 1-3 without prejudice or disclaimer of the subject matter contained therein.

Please add claims 6-10 as follows:

*add as*  
*Sub 52*

--6. A semiconductor device comprising:  
a gate formed on an active region of a substrate;  
a field oxide formed on the substrate adjacent the active region;  
a protective layer formed on a said field oxide, said protective layer being a material different than said field oxide;  
an insulating layer formed on the substrate including said gate, said field oxide and said protective layer;  
a contact hole formed through said insulating layer; and  
a connecting wire coupled to said gate through said contact hole.

7. The semiconductor device of claim 6, wherein said protective layer is a polysilicon layer.

8. The semiconductor device of claim 6, wherein said protective layer is formed on said field oxide only.

*Sub 52*

9. The semiconductor device of claim 6, wherein said gate is a MOSFET gate.